

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2131	(sr strontium) near2 (zirconate zirconium zr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L2	96	szo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L3	25167	(perovskite superlattice)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L4	2221	L1 L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L5	125	L4 with L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L6	2030965	memory thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
L7	70	L5 and L6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:22
L8	172402	(programmable perovskite complex conduct\$4 resist\$4) adj2 metal pcmo LSMO GBCO CMR adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L9	1646545	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L10	4832396	conduct\$4 resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02

L11	5558	L10 adj L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L12	434	L11 and L8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L13	1177418	(dop\$4 impurit\$3 (ion near3 implant\$3) diffus\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L14	341	L12 and L13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L15	1140	L11.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
L16	72	L15 and L14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:30
L17	14963	(programmable perovskite complex conduct\$4 resist\$4) adj metal adj oxide pcmo LSMO GBCO PCRAM CMR adj oxide HTSC high adj temperature adj2 superconduct\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:30
L18	1098358	((multi\$4 multiplicit\$3 plural\$4 dual) adj (layer film) multilayer\$3 sublayer\$3 (multi sub) adj layer\$3 layered laminat\$4 Tripart\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:38
L19	245	18 near2 17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:38
L20	245	19 not 16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:39

L21	243	19 not 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:39
L22	20	19.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:40
L23	1646545	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:40
L24	1	23 near9 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:40
L25	4	23 same 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:45
L26	1177418	(dop\$4 impuri\$3 (ion near3 implant\$3) diffus\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:45
L27	1	25 and 26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:45
S1	0	10/753914	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 11:07
S2	1	09/948877	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 07:52
S3	1736	"KONINKLIJKE PHILIPS" as.	USPAT	OR	ON	2003/08/19 13:35
S4	6134	(programmable perovskite complex conduct\$4 resist\$4) adj metal adj oxide pcmo LSMO GBCO CMR adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:04

S5	166335	(programmable perovskite complex conduct\$4 resist\$4) adj2 metal pcmo LSMO GBCO CMR adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:58
S6	2	"6204139" pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:02
S7	23	("6204139").URPN.	USPAT	OR	ON	2005/01/25 15:03
S8	2357617	conduct\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:05
S9	248412	metal\$4 adj (oxide oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:06
S10	8822907	first bottom lower down	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:08
S11	7816625	second top upper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:44
S12	1646569	oxide oxidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:23
S13	31608	S8 adj3 S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:28
S14	4348	S8 adj S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:28
S15	1	09/826386	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:29

S16	1061989	((multi\$4 multiplicit\$3 plural\$4) adj (layer film) multilayer\$3 sublayer\$3 (multi sub) adj layer\$3 layered laminat\$4 Tripart\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 15:31
S20	30476986	(@ad @pd) <"20031023"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:22
S22	2	S16 adj S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:26
S23	768	S10 adj S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:35
S24	483	S11 adj S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:36
S25	74	S23 same S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:37
S26	1590437	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:37
S27	14	S25 same S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:39
S28	14	S27 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/25 16:40
S29	14	S27 and S23 and S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21

S30	2361216	conduct\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S31	8833677	first bottom lower down	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S32	7826787	second top upper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S33	1648995	oxide oxidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S34	31698	S30 adj3 S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S35	769	S31 adj S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S36	484	S32 adj S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S37	74	S35 same S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S38	1593781	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21
S39	14	S37 same S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:21

S40	14	S39 and S35 and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:44
S41	146796	sharp as	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 07:44
S42	166754	(programmable perovskite complex conduct\$4 resist\$4) adj2 metal pcmo LSMO GBCO CMR adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:53
S43	1593781	memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:06
S44	71	S42 adj2 S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:06
S45	4724557	conduct\$4 resist\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:10
S46	5235	S45 adj S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:59
S47	126	S41 and S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:12
S48	37	S47 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:23
S49	375	S46 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:37

S50	1144585	(dop\$4 impurit\$3 (ion near3 implant\$3) diffus\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:39
S51	1461577	active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:40
S52	728174	(S42 S45 S51) adj (film layer material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:42
S53	18614	S50 near2 S52	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 08:42
S54	45	S49 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:36
S55	290	S49 and S50	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:52
S56	31	S42 near S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:52
S57	1015	S42 with S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:53
S58	122	S55 and S57	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:58
S59	290	S46 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:58

S60	1072	S46.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 09:58
S61	56	S60 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 09:02
S62	10584	S45 adj2 S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 10:02
S63	290	S55 and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 10:02
S64	2250	S62.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 10:02
S65	298	S55 and 36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 10:02
S66	63	S55 and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 10:02
S67	15	("5,666,217" "6,323,525" "6,473,332" "6,774,054").pn. "20040109351" "20040235247" 10/605757	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:01
S68	2066	(sr strontium) near2 (zirconate zirconium zr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 09:47
S69	89	szo	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:09

S70	6	S68 and S69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 09:47
S71	24256	(perovskite superlattice)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:10
S72	2149	S68 S69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:10
S73	119	S72 with S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:10
S74	1966924	memory thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 08:11
S75	64	S73 and S74	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:58
S76	1034	(sr strontium) near (zirconate zirconium zr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/28 09:47